

KK1600-FAST SWITCHING THYRISTOR

1800-2000 V_{DRM}

HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability

ELECTRICAL CHARACTERISTICS AND RATINGS KK1600-FAST SWITCHING THYRISTOR**Gating**

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	$V_D=12V; R_L=30\Omega; T_j=+25^{\circ}C$
Gate- trigger voltage	V_{GT}	0.70	2.5		V	$V_D=12V; R_L=30\Omega; T_j=+25^{\circ}C$
Peak negative voltage	V_{GRM}		5		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t_d		3.0	2.5	s	$I_{TM}=1000A; V_D=67\%V_{DRM}$ Gate pulse: $V_G=30V; R_G=10\Omega$; $t_r=0.1\text{ s}; t_p=20\text{ s}$



